Absolute Maximum Ratings at T_j=25 unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	±30	V
Continuous drain current[1], T_C=25 °C	I_D	80	A
Continuous drain current[1], T_C=100 °C		50	
Pulsed drain current[2], T_C=25 °C	$I_{D, pulse}$	240	A
Continuous diode forward current[1], T_C=25 °C	I_S	80	A
Diode pulsed current[2], T_C=25 °C	$I_{S, pulse}$	240	A
Power dissipation[3] T_C=25 °C	P_D	455	W
Single pulsed avalanche energy[5]	E_{AS}	1700	mJ
MOSFET dv/dt ruggedness, V_{DS} 480 V	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS} 480 V, I_{SD} D	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R	0.27	°C/W
Thermal resistance, junction-ambient[4]	R	62	°C/W

Electrical Characteristics at T_j=25 unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	V_{GS}=0 V, I_D=2 mA
		700				V_{GS}=0 V, I_D=2 mA, T_j=150 °C
Gate threshold voltage	$V_{GS(th)}$	2.8		4.0	V	V_{DS}=V_{GS}, I_D=2 mA
Drain-source on-state resistance	$R_{DS(ON)}$		0.028	0.035		V_{GS}=10 V, I_D=40 A
			0.075			V_{GS}=10 V, I_D=40 A, T_j=150 °C
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=30 V
				-100		V_{GS}=-30 V
Drain-source leakage current	I_{DSS}			5	A	V_{DS}=650 V, V_{GS}=0 V
Gate resistance	R_G		2.4			= 1 MHz, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}				pF	V_{GS}=0 V, V_{DS}=50 V, 00 kHz
Output capacitance	C_{oss}		447.1		pF	
Reverse transfer capacitance	C_{rss}		13.2		pF	
Turn-on delay time	$t_{d(on)}$		52.3		ns	V_{GS}=10 V, V_{DS}=400 V, R_G=5 I_D=40 A
Rise time	t_r		86.8		ns	
Turn-off delay time	$t_{d(off)}$		165.2		ns	
Fall time	t_f		8.5		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		153.6		nC	V_{GS}=10 V, V_{DS}=400 V, I_D=40 A
Gate-source charge	Q_{gs}		41.8		nC	
Gate-drain charge	Q_{gd}		50.2		nC	
Gate plateau voltage	$V_{plateau}$		5.8		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	I_S=80 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		566.1		ns	, I_S=40 A,
Reverse recovery charge	Q_{rr}		13.2		C	
Peak reverse recovery current	I_{rrm}		45.9		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.

Figure 7. Forward characteristic of body diode

Figure 8. Drain-source on-state resistance

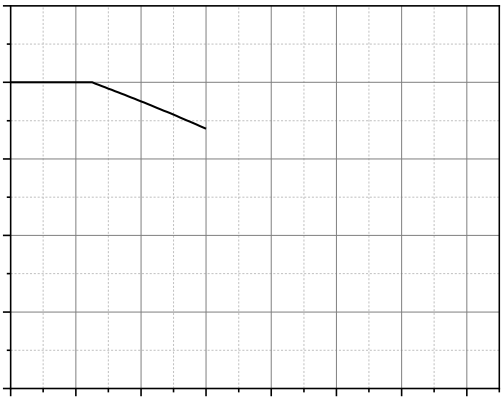


Figure 9. Drain current

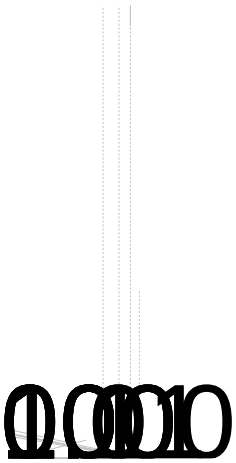


Figure 10. Safe operation area

Test circuits and waveforms

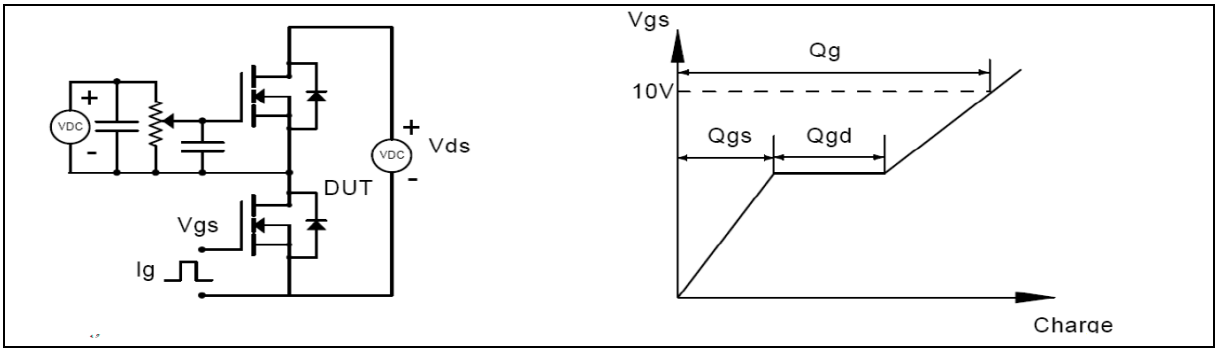


Figure 1. Gate charge test circuit & waveform

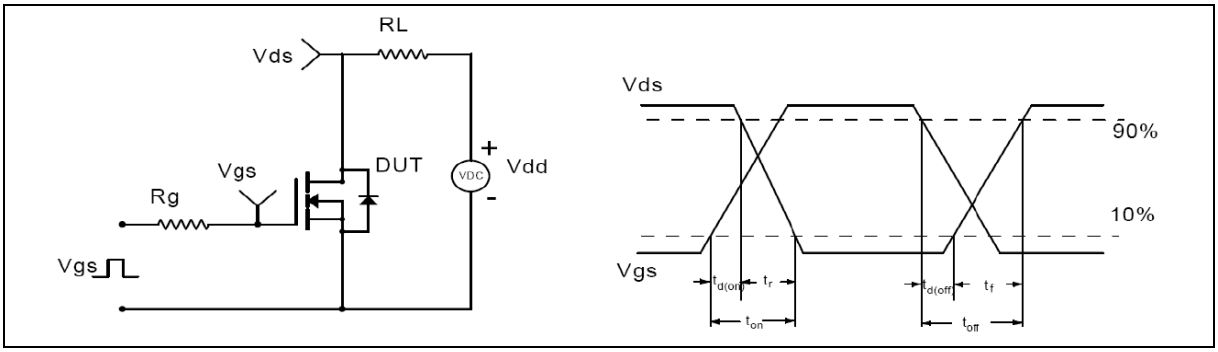


Figure 2. Switching time test circuit & waveforms

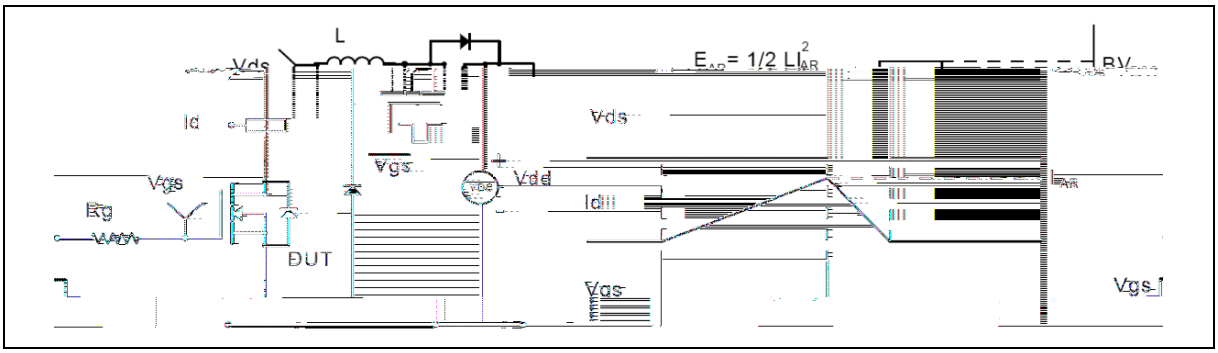


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

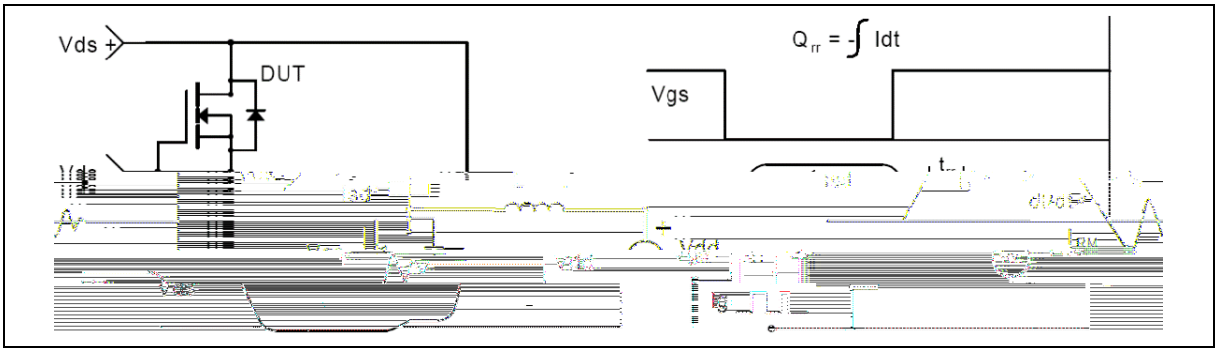
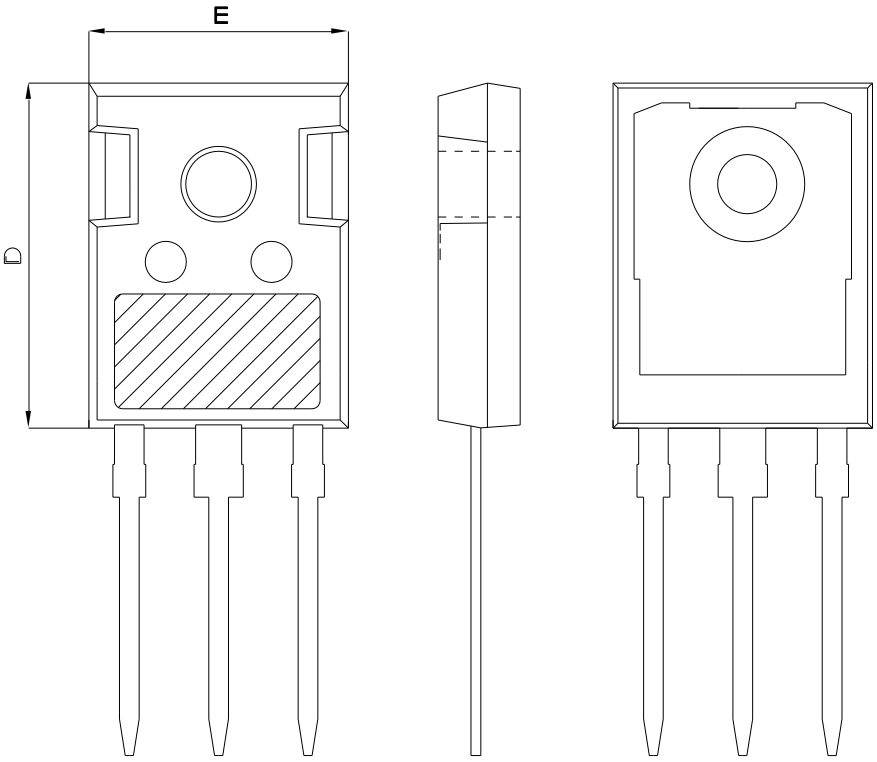


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44 BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
	3.40	3.60	3.80
	-	-	7.30
S	6.15 BSC		

Version1: TO247-C package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO247-C	30	11	330	6	1980

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R035HTF	TO247	yes	yes	yes

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